

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	198	(endo-akihiko or nishihata-hideki).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:03
S2	82	(endo-akihiko or nishihata-hideki).in. and wafer	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:04
S3	105	(endo-akihiko or nishihata-hideki).in. and (wafer or semiconductor)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:04
S4	81	(endo-akihiko or nishihata-hideki).in. and (wafer or semiconductor) and (@pd<"20060306" or @ad<"20060306")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:05
S5	37	(endo-akihiko or nishihata-hideki).in. and (wafer or semiconductor) and (bond\$3) and (@pd<"20060306" or @ad<"20060306")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:06
S6	0	(endo-akihiko or nishihata-hideki).in. and (wafer or semiconductor) and (bond\$3) and (spher\$5) and (@pd<"20030908" or @ad<"20030908")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:19
S7	2	"5374564".pn.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/26 14:20
S8	358	("4931405" "5034343" "5198371").PN. OR ("5374564").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:20
S9	358	("4931405" "5034343" "5198371").PN. OR ("5374564").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:21
S10	1	"6756285".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:21
S11	1	"6004860".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:38
S12	1	"6583029".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:39

S13	1	"6756285".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:44
S14	1	"6583029".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 14:57
S15	0	wafer near10 bond\$3 near10 (curv\$5 or spher\$5) near10 epitaxial near10 (oxide or insulat \$4) near10 (implantat\$4) near10 (hydrogen or noble) near10 heat near10 separat\$4	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:22
S16	0	(wafer or plate or substrate or silicon) near10 bond\$3 near10 (curv\$5 or spher\$5) near10 epitaxial near10 (oxide or insulat \$4) near10 (implantat\$4) near10 (hydrogen or noble) near10 heat near10 separat\$4	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:22
S17	0	(wafer or plate or substrate or silicon) same bond\$3 same (curv \$5 or spher\$5) same epitaxial same (oxide or insulat\$4) same (implantat\$4) same (hydrogen or noble) same heat same separat \$4	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:23
S18	0	(wafer or plate or substrate or silicon) same bond\$3 same (curv \$5 or spher\$5) same epitaxial same (oxide or insulat\$4) same (implant\$4) same (hydrogen or noble) same heat same separat \$4	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:24
S19	4	(wafer or plate or substrate or silicon) same bond\$3 same epitaxial same (oxide or insulat \$4) same (implant\$4) same (hydrogen or noble) same heat same separat\$4	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:25
S20	712	257/618.ccls.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:28
S21	1671	438/455.ccls.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:28
S22	190	(wafer or plate or substrate or silicon) same (bond\$3 or separat \$4) same epitaxial same (oxide or insulat\$4) same (implant\$4 or diffus\$4) same (hydrogen or noble) same (heat or anneal\$3 or temperature or celsius)	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:49
S23	120	S22 and (@pd< "20030908" or @ad< "20030908")	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 15:51
S24	4	("2001/0029072").URPIN.	USPAT	ADJ	ON	2008/03/26 15:56

S25	47	("4058418" "4774194" "4778478" "4816420" "5277748" "5371037" "5391257" "5492859" "5536361" "5811348" "5840610" "5856229" "5966620").PN. OR ("6190937").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 16:03
S26	16	("5371037" "5374564" "5458755" "5726464" "5811348" "5856229" "5966620" "6107213").PN. OR ("6468923").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/26 16:07
S27	4	("2001/0029072").URPN.	USPAT	ADJ	ON	2008/03/26 16:14
S28	0	ep "0410679"	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:33
S29	0	ep0410679	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:33
S30	0	ep-0410679	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S31	2	"0410679".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S32	0	"ep0410679".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S33	0	"ep 0410679".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S34	0	"ep-0410679".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S35	744	nakazato.in.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:34
S36	0	nakazato.in. and "410679"	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:35
S37	112	nakazato.in. and ep	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:35
S38	0	"nakazato et al."	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:35
S39	1	"5854123".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:36
S40	1	"5909627".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:37
S41	1	"6255731".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:37
S42	1	"5362667".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:40
S43	5	"0410679"	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:55
S44	1	"20070069335"	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 08:59
S45	1	"5374564".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 09:31

S46	1583	(wafer or plate or substrate or silicon) same (bond\$3 or separat \$4) same (different) same (thick \$4) same (first or front or top) same (second or bottom or rear or back) same oxide	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:26
S47	84	(wafer or plate or substrate or silicon) same (bond\$3 or separat \$4) same (different) same (thick \$4) same (first or front or top) same (second or bottom or rear or back) same oxide same epitaxial	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:27
S48	74	(@pd<"20030908" or @ad<"20030908") and S47	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:28
S49	32	(wafer or plate or substrate or silicon) same (bond\$3) same (different) same (thick\$4) same (first or front or top) same (second or bottom or rear or back) same oxide same epitaxial	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:30
S50	0	(wafer or plate or substrate or silicon) same (bond\$3) same (different) same (thick\$4) same (first or front or top) same (second or bottom or rear or back) same oxide same epitaxial same (warp\$4)	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:31
S51	1	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4) same (first or front or top) same (second or bottom or rear or back) same oxide same epitaxial same (warp \$4)	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:31
S52	168	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4) same (first or front or top) same (second or bottom or rear or back) same oxide same (warp\$4)	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:35
S53	204	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4) same (first or front or top) same (second or bottom or rear or back) same oxide same (warp\$4 or curv\$4)	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:35
S54	87	S53 and (@pd<"20030908" or @ad<"20030908")	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:36
S55	85	S54 not S49	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 10:36

S56	0	("2007/0069335").URPN.	USPAT	ADJ	ON	2008/03/27 11:14
S57	59	(endo-akihiro or nishihatahideki).in. and (bond\$3)	US-PGPUB; USPAT; FPFS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/27 11:15
S58	0	S57 and (@pd< "20030908" or @ad< "20030908")	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:15
S59	964	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4 or length or width) same (first or front or top) same (second or bottom or rear or back) same (warp\$4 or curv\$4)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:21
S60	809	S59 and (@pd< "20030908" or @ad< "20030908")	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:22
S61	6	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4 or length or width) same (first or front or top) same (second or bottom or rear or back) same (warp\$4 or curv\$4) same epitaxial	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:23
S62	336	(wafer or plate or substrate or silicon) same (bond\$3) same (different or thinner or thicker) same (thick\$4 or length or width) same (first or front or top) same (second or bottom or rear or back) same (warp\$4 or curv\$4) same (oxide or insulat\$4)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:24
S63	207	S62 and (@pd< "20030908" or @ad< "20030908")	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:25
S64	602	S60 not S63	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:26
S65	9258	(257/618,e21.567,e21.122,e21.508,e23.021.ccls.) or (438/455,459,406.ccls.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:33
S66	5843	S65 and (bond\$3 near10 (wafer or silicon or substrate or plate))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:34
S67	3753	S66 and (@pd< "20030908" or @ad< "20030908")	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 11:34
S68	1	("2003/0020096").URPN.	USPAT	ADJ	ON	2008/03/27 13:27
S69	0	("2003/0040163").URPN.	USPAT	ADJ	ON	2008/03/27 13:29

S70	2	"6756285".pn.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/27 16:32
S71	14	("5261999" "5310451" "5362667" "5373184" "5728623" "5753134" "5854123" "5909627" "6143628" "6255731").PN. OR ("6756285").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:32
S72	1	"6255731".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:49
S73	1	"6143628".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:50
S74	1	"5909627".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:51
S75	1	"5854123".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:51
S76	1	"5753134".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:51
S77	1	"5728623".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:52
S78	1	"5373184".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:53
S79	1	"5362667".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:53
S80	1	"5310451".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:53
S81	1	"5261999".pn.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:53
S82	2	"4939101".pn.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/27 16:55
S83	2	"4878957".pn.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/27 16:55
S84	2	"4830984".pn.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/27 16:55

S85	34	("3458369" "3808674" "3821033" "3821039" "3836999" "3914136" "3962716" "3997368" "4079506" "4131487" "4159214" "4415373" "4548658" "4631804").PN. OR ("4830984").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:56
S86	42	("4017341" "4638552" "4738935" "4774196" "4830984" "4878957" "4939101").PN. OR ("5071785").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/27 16:58
S87	21119	(257,618,625,676,779-785, e21.087-e21.088,e21.567, e21.122-e21.128,e21.48,e21.508, e21.512,e21.519,e21.567, e23.021,e27.137,e27.144, e27.161,e23.023,e23.077.ccls.) or (438/188,455-459,406,615-617.ccls.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/28 08:10
S88	4645	S87 and ((insulat\$4 or oxide or nitride or isolat\$4) near10 thickness)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/28 08:11
S89	471	S87 and ((insulat\$4 or oxide or nitride or isolat\$4) near10 thickness near10 (top or first or front) near10 (bottom or back or rear or second))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/28 08:12
S90	279	S89 and (@pd< "20030908" or @ad< "20030908")	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/28 08:13
S91	14	("2003/0064569").URPN.	USPAT	ADJ	ON	2008/03/28 08:23
S92	0	"6756285.pn"	USPAT	ADJ	ON	2008/03/28 09:14
S93	1	"6756285".pn.	USPAT	ADJ	ON	2008/03/28 09:14
S94	0	"20070069335".pn.	USPAT	ADJ	ON	2008/03/28 09:54
S95	0	"20070069335"	USPAT	ADJ	ON	2008/03/28 09:55
S96	0	"20070069335".pn.	USPAT	ADJ	ON	2008/03/28 09:56
S97	0	"20070069335"	USPAT	ADJ	ON	2008/03/28 09:57
S98	5	"6756285"	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/03/28 10:05
S99	33	"5362667"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/28 14:34

S100	2	"5362667".pn.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/28 14:35
------	---	---------------	---	-----	----	---------------------

3/ 28/ 2008 5:31:47 PM

C:\Documents and Settings\mhung\My Documents\EAST\Workspaces\ 10570665.wsp